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November 2013

FDP047N10

N-Channel PowerTrench $^{\mbox{\it lh}}$ MOSFET 100 V, 164 A, 4.7 m Ω

Features

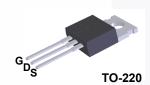
- $R_{DS(on)}$ = 3.9 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 75 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- · High Power and Current Handling Capability
- RoHS Compliant

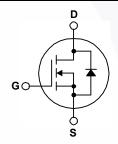
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- · Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies
- · Micro Solar Inverter





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FDP047N10	Unit
V _{DSS}	Drain to Source Voltage	100	V	
V _{GSS}	Gate to Source Voltage	±20	V	
	Drain Current - Continuous (T _C =	25°C, Silicon Limited)	164*	Α
I _D	- Continuous (T _C = 1	00°C, Silicon Limited)	116*	Α
	- Continuous (T _C =	25°C, Package Limited)	120	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	656*	Α
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	1153	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns
Б	$(T_C = 25^{\circ}C)$		375	W
P_{D}	Power Dissipation - Derate Abov	re 25°C	2.5	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C	
T _L	Maximum Lead Temperature for Soldering, 1/8"	from Case for 5 Seconds	300	οС

^{*}Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120A.

Thermal Characteristics

Symbol	Parameter	FDP047N10	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP047N10	FDP047N10	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$	100	-	-	V
ΔBV _{DSS} / ΔΤ _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	-	0.1	-	V/°C
1	Zoro Coto Voltago Droin Current	V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	
I _{DSS} Zero Gate Voltage Drain Current	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μA	
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	2.5	3.5	4.5	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 75 A	-	3.9	4.7	mΩ
9 _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 75 A	-	170	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 25 V V - 0 V	-	11500	15265	pF
C _{oss}	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz	-	1120	1500	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1011 12	-\	455	680	pF

Switching Characteristics

_						
t _{d(on)}	Turn-On Delay Time		-	174	358	ns
t _r	Turn-On Rise Time	$V_{DD} = 50 \text{ V}, I_D = 75 \text{ A},$	-	386	782	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_{G} = 25 \Omega$	-	344	698	ns
t _f	Turn-Off Fall Time	(Note 4)	-	244	499	ns
Q _{g(tot)}	Total Gate Charge at 10V	V _{DC} = 80 V I _D = 75 A	-	160	210	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DS} = 80 \text{ V}, I_{D} = 75 \text{ A},$ $V_{GS} = 10 \text{ V}$	-	56	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	36	-	nC

Drain-Source Diode Characteristics

Is	Maximum Continuous Drain to Source Diode Forward Current		-	-	164*	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	656	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 75 A	-	-	1.25	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 75 A,	-	88	-	ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt = 100 A/μs	-	245	/ -	nC

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 0.41 mH, I $_{AS}$ = 75 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C. 3. I $_{SD}$ \leq 75 A, di/dt \leq 200 A/ μ s, V $_{DD}$ \leq BV $_{DSS}$, starting T $_{J}$ = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

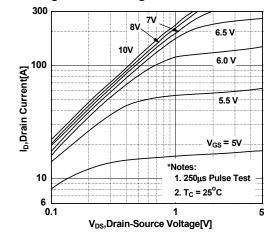


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

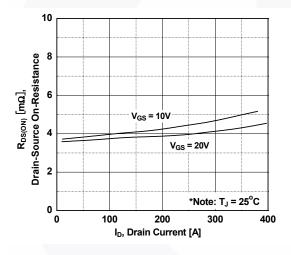


Figure 5. Capacitance Characteristics

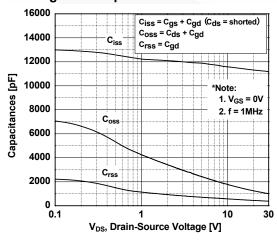


Figure 2. Transfer Characteristics

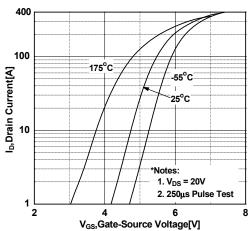


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

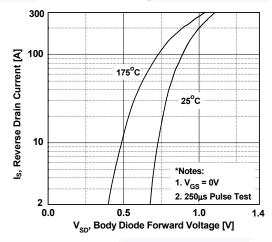
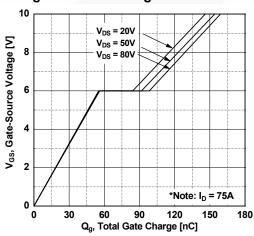


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

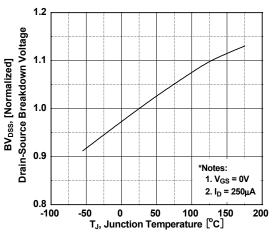


Figure 8. On-Resistance Variation vs. Temperature

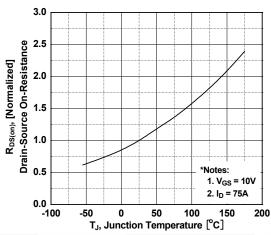


Figure 9. Maximum Safe Operating Area

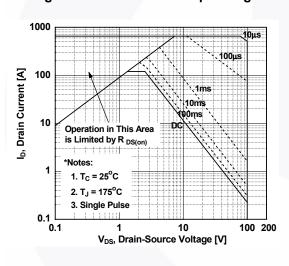


Figure 10. Maximum Drain Current vs. Case Temperature

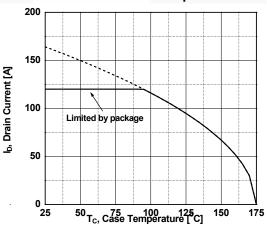
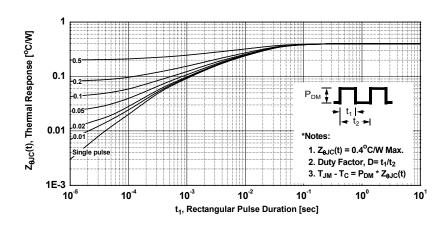


Figure 11. Transient Thermal Response Curve



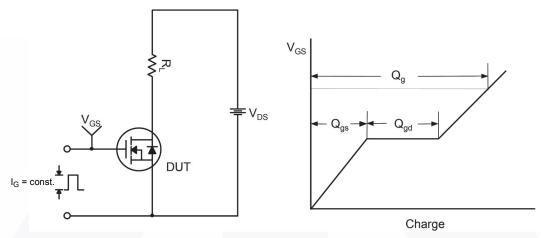


Figure 12. Gate Charge Test Circuit & Waveform



Figure 13. Resistive Switching Test Circuit & Waveforms

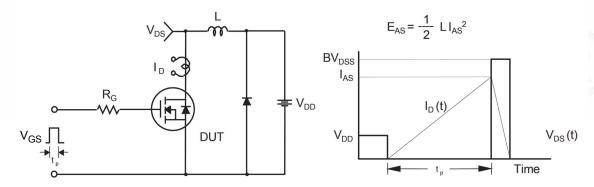


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

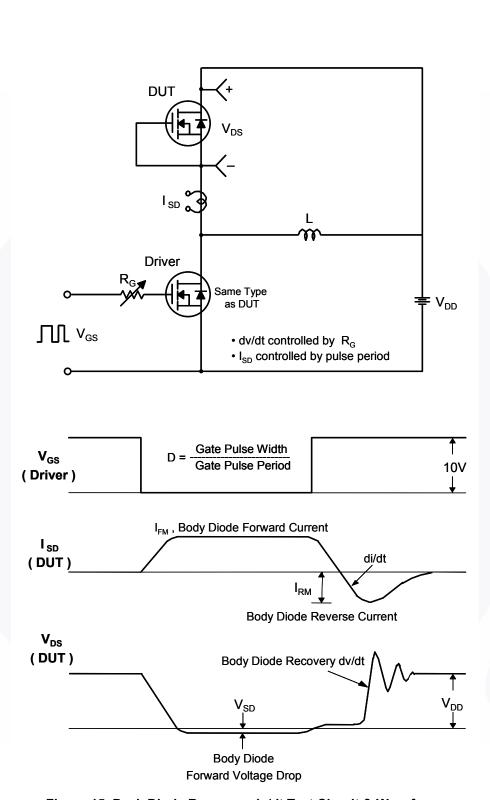


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

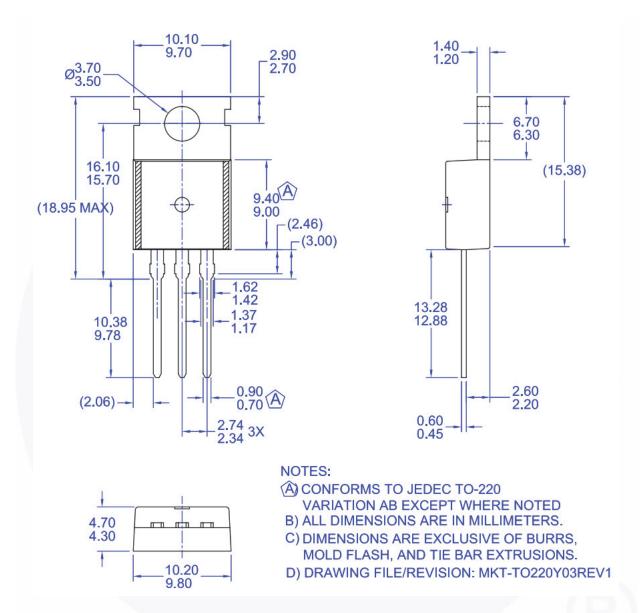


Figure 16. TO220, Molded, 3-Lead, Non Jedec Variation AB

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